



1753

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In the Application of:

Inventors : Alexander Leybovich
Serial No. : 10/624,384
Filed : July 22, 2003
Title : Method and Apparatus for Deposition
Of Low-K Dielectric Materials
Docket No. : 020324 227P2
Customer No.: 33805

INFORMATION DISCLOSURE STATEMENT

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P.O. Box 1450
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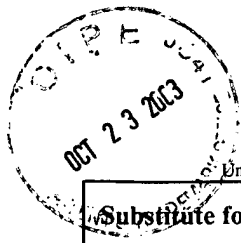
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Respectfully submitted,

By Danielle Skoczen
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				Application Number	10/624,384
				Filing Date	July 22, 2003
				First Named Inventor	Leybovich
				Art Unit	
				Examiner Name	
Sheet	1	of	3	Attorney Docket Number	020324 227P2

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number Number - Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	AA	US-6,395,649	05-28-2002	Wu, Hui-Jung	
	AB	US-6,340,435	01-22-2002	Bjorkman et al.	
	AC	US-			
	AD	US-			
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FOREIGN PATENT DOCUMENTS

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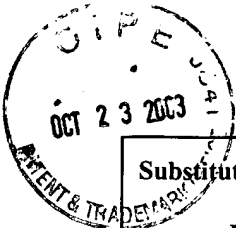
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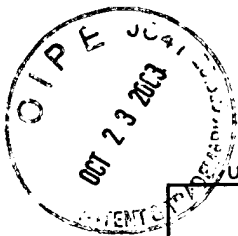
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	AJ	BALIGA, J.; Low-k Dielectrics Enable Faster Chips, Design News: Semiconductor Manufacturing, June 3, 2002, pp. S/13-S14			
	AK	CHAPMAN, B.; DC Glow Discharges, pp. 98-101			
	AL	THOMAS, MICHAEL E.; Spin-On Stacked Films for Low-k _{eff} Dielectrics, Solid State Technology, July 2001, pp. 105-113			
	AM	MAISSEL, Leon and GLANG, Reinhard; Handbook of Thin Film Technology, pp. 3-14—30-15, 3-24—3-27, 4-26—4-37, McGraw Hill Book Company			
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	AP	SHIMOKAWA, F.; High-Power Fast-Atom Beam Source and Its Application to Dry Etching, J. Vac. Sci. Technol. A10(4), July/Aug. 1992, pp. 1352-1357			
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	AR	SHIMOKAWA, F. and NAGAI, K.; A Low-Energy Fast-Atom Source, Nuclear Instruments and Methods in Physics Research B33 (1988) pp. 867-870			
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	AU	GORBATOV, Y., VYATKIN, A. and ZINENKO, V.; A Low-Energy Fast-Atom Beam Source, Nuclear Instruments and Methods in Physics Research B55 (1991) 328-330	
	AV	Sputter Etching and Deposition of Insulators, pp. 195-197	
	AW	CHAPMAN, B.; Glow Discharge Processes, Sputtering and Plasma Etching, pp. 38-41, John Wiley & Sons (1980)	
	AX	CHEUNG et al.; Integration and Characterization of Low Carbon Content SiO/subx/C/suby/H/subz/ Low K Materials for <0.18 mu m Dual Damascene Application; Materials Research Society Symposium Proceedings, Vol. 612, 2000 (Abstract)	
	AY	MOUNTSIER et al.; Integration Studies of Plasma Deposited Fluorinated Amorphous Carbon, Low-Dielectric Constant Materials IV Symposium, pp. 259-64 1998 (Abstract)	
	AZ	MOUNTSIER, T. and SAMUELS, J.; Precursor Selection for Plasma Deposited Fluorinated Amorphous Carbon Films; Thin Solid Films (Switzerland) Vol. 332, 2 Nov. 1998 (Abstract)	
	BA	YU et al.; Low K Film Etch in Applied Materials eMxP Plus Chamber; Materials Research Society Symposium - Proceedings, 1999 (Abstract)	
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	BC	BARSKAYA, A. YA. et al; Sputtering of Different Materials by Ions and Atoms, Journal of Technical Physics, v57, 6, 1987, pp 1223-1225 (Accompanied with two English abstracts)	

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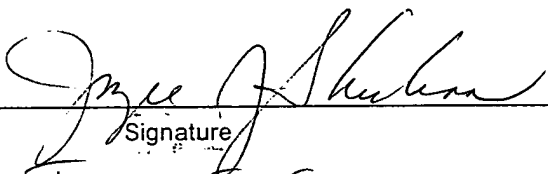
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